

SIMULATION OF OXYGEN IMPLANTED DISTRIBUTION
FOR SOI STRUCTURE

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SOI structure is thought to be the solution of many submicron CMOS problems [1]. However, hitherto, the distribution profile of oxygen ions in single crystal silicon has not been simulated in the VLSI process simulators. In this paper, we give out the oxygen implanted distribution model based on the statistical method. Due to its accuracy and simplicity, it is especially available for the process simulators. Also this model can be expanded to the simulation of the distribution of other reactive ions, as well as nonreactive ions such as B, P and As.

First, we discuss the relationship between the threshold dose $Dose_{th}$ and implantation energy E (see Fig.1), where the $Dose_{th}$ is a minimum implantation dose value in a given E for forming buried oxide insulation layer. It can be expressed by Taylor series to the third order of E , that is :

$$Dose_{th} = \sum_{i=1}^3 b(i) \cdot E^i \quad (1)$$

Where

$$b(1)=4.827 \times 10^{-5}, b(2)=3.345 \times 10^{-6}, b(3)=-1.075 \times 10^{-7}$$

Second, a concentration-position relationship of oxygen ions implanted in silicon is presented using quasi-half-gaussian frequency function [2] which is written as :

$$f(x) = \frac{1}{\sqrt{\pi} \cdot \sigma_1 / 2 + (Rm_1 - Rm_2) + \sqrt{\pi} \cdot \sigma_2 / 2}$$

$$\begin{cases} \exp\left[-\frac{(x-Rm_1)^2}{2 \cdot \sigma_1^2}\right] & x < Rm_1 \\ 1 & Rm_1 \leq x \leq Rm_2 \\ \exp\left[-\frac{(x-Rm_2)^2}{2 \cdot \sigma_2^2}\right] & x > Rm_2 \end{cases} \quad (2)$$

The impurity ion concentration $c(x)$ can be determined by :

$$c(x) = Dose \cdot f(x) \quad (3)$$

Fig.2 shows the results of using quasi-half-gaussian function to fit the experiment data from [3]. Table 1 shows the value of Rm_1 , Rm_2 , σ_1 , σ_2 extracted from experiment curves [3].

The general relationship between anyone of Rm_1 , Rm_2 , σ_1 , σ_2 and E , Dose is sought by applying linear regression statistical method. Rm_1 , Rm_2 can be expressed as

$$Rm_{1,2} = A(1) \cdot E + A(2) \cdot E^2 + A(3) \cdot E^3 + A(4) \cdot Dose + A(5) \cdot Dose^2 + A(6) \cdot E \cdot Dose \quad (4)$$

σ_1 , σ_2 can be expressed as :

$$\sigma_{1,2} = B(1) + B(2) \cdot E + B(3) \cdot E^2 + B(4) \cdot Dose + B(5) \cdot Dose^2 + B(6) \cdot E \cdot Dose \quad (5)$$

All coefficients $A(i)$, $B(i)$ and other detail information about statistical analysis are included in Table 2, where $SQRENE = E^2$, $CUDENE = E^3$, $SQRDOS = Dose^2$, $CROSS = E \cdot Dose$. We may note that R -squared value is greater than 0.9, which is the general accepted criteria for a statistical model, the modulus of T -STATS and F values are big, 2-TAIL SIG. approach zero and Durbin-waston statistical value are not far from 2.0, all of the preceding statistical criteria value indicates that our model is acceptable [4]. The comparison between the real distribution of oxygen ions [3] and our simulated value is given in Fig.3. Calculations show that the singular comparison accuracy of our model is within 4%

References :

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- (4) Ingram olkin, et al., Probability Models and Applications, Macmillan Publishing co, Inc.

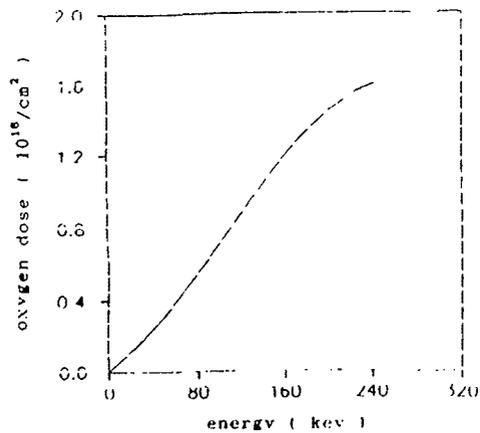


Fig.1 threshold dose versus ion implantation energy for oxygen.

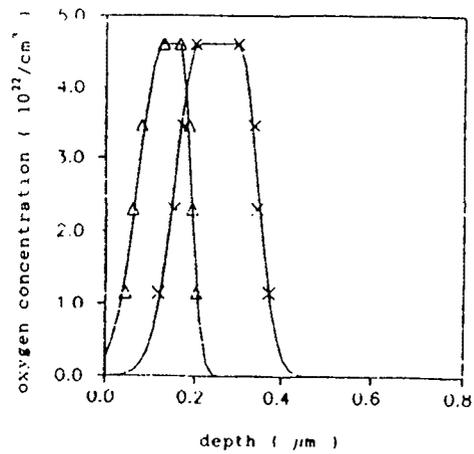


Fig.2 oxygen ion distribution profile
— theoretically fitted curves.

△△△, experiment (E=50keV, Dose=4.28x10¹⁷/cm²),
xxx, experiment (E=100keV, Dose=5.35x10¹⁷/cm²).

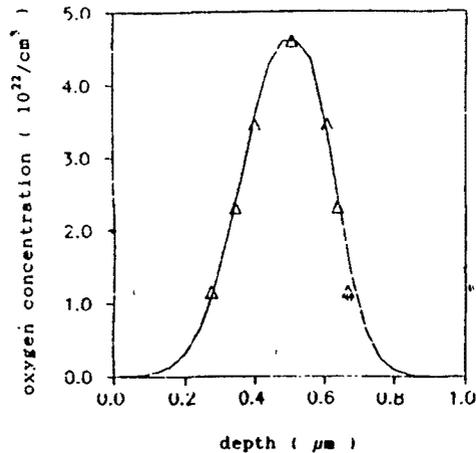


Fig.3 oxygen ion distribution profile
— simulated, △△△ experiment

(E = 200 keV , Dose = 1.41x10¹⁸/cm²).

Table 1 $R_{M1}(\mu m), R_{M2}(\mu m), \sigma_1(\mu m), \sigma_2(\mu m)$ extracted from experiment data (unit for Energy : keV, for Dose : x 10¹⁶/cm²).

obs	RM1	RM2	SIGMA1	SIGMA2	ENERGY	DOSE
1	0.373984	0.582446	0.082372	0.078559	200.0000	1.840610
2	0.442552	0.564393	0.100950	0.077559	200.0000	1.589610
3	0.500536	0.588342	0.134265	0.108058	200.0000	1.366170
4	0.500791	0.500845	0.120756	0.096964	200.0000	0.991209
5	0.124160	0.164955	0.051359	0.023705	50.00000	0.615791
6	0.205026	0.299569	0.050050	0.042706	100.0000	0.969601
7	0.407993	0.417489	0.138774	0.067449	150.0000	1.230390

VARIABLE	COEFFICIENT	STD. ERROR	T-STAT.	2-TAIL SIG.
ENERGY	-0.0315020	0.0081522	-3.8642217	0.001
SORENE	0.0002698	6.545E-05	4.1221238	0.000
CUBENE	-5.421E-07	1.216E-07	-4.4568498	0.001
DOSE	2.3811465	0.5751319	4.1439999	0.001
SORIOS	-0.2747252	0.0710753	-3.8652715	0.001
CROSS	-0.0087998	0.0031285	-2.8125675	0.017

R-squared 0.998931 Mean of dependent var 0.364995
Adjusted R-squared 0.993584 S.D. of dependent var 0.146252
S.E. of regression 0.011715 Sum of squared resid 0.000117
Durbin-Watson stat 1.369757 F-statistic 186.8297
Log Likelihood 28.08641

(a)

VARIABLE	COEFFICIENT	STD. ERROR	T-STAT.	2-TAIL SIG.
E	0.7929971	0.2559245	3.0985590	0.009
ENERGY	0.0152850	0.0045128	3.3699267	0.004
DOSE	-2.7237912	0.0714982	-3.8254411	0.001
SORENE	-9.729E-05	2.018E-05	-4.8268894	0.000
SORIOS	-0.1265824	0.0323290	-3.9175181	0.000
CROSS	0.0151555	0.0042764	3.5419472	0.001

R-squared 0.977585 Mean of dependent var 0.896912
Adjusted R-squared 0.865512 S.D. of dependent var 0.037802
S.E. of regression 0.011578 Sum of squared resid 0.000184
Durbin-Watson stat 1.369757 F-statistic 8.722740
Log Likelihood 26.97752

(c)

VARIABLE	COEFFICIENT	STD. ERROR	T-STAT.	2-TAIL SIG.
ENERGY	0.0025037	0.0154061	0.1677062	0.894
SORENE	-5.895E-07	0.0001237	-0.0047658	0.997
CUBENE	7.467E-09	2.299E-07	0.0324812	0.979
DOSE	0.0541178	1.0864918	0.0497914	0.968
SORIOS	0.0075753	0.1343189	0.0519956	0.632
CROSS	-0.0009816	0.0059122	-0.1660326	0.895

R-squared 0.996493 Mean of dependent var 0.414006
Adjusted R-squared 0.978959 S.D. of dependent var 0.152423
S.E. of regression 0.022139 Sum of squared resid 0.000490
Durbin-Watson stat 1.369757 F-statistic 56.83125
Log Likelihood 23.55107

(b)

VARIABLE	COEFFICIENT	STD. ERROR	T-STAT.	2-TAIL SIG.
E	0.0049672	0.2771785	0.0179206	0.989
ENERGY	0.0002917	0.0040867	0.0596930	0.962
DOSE	0.0215261	0.9438656	0.0228063	0.985
SORENE	-1.018E-06	1.052E-05	-0.0591184	0.962
SORIOS	-0.0795765	0.0891661	-0.8824518	0.536
CROSS	0.0008114	0.0046316	0.1745059	0.887

R-squared 0.957866 Mean of dependent var 0.069571
Adjusted R-squared 0.747197 S.D. of dependent var 0.029230
S.E. of regression 0.014697 Sum of squared resid 0.000216
Durbin-Watson stat 1.369757 F-statistic 4.546784
Log Likelihood 26.41906

(d)

Table 2 statistical analysis results of (a)RM₁, (b)RM₂, (c)σ₁, (d)σ₂.